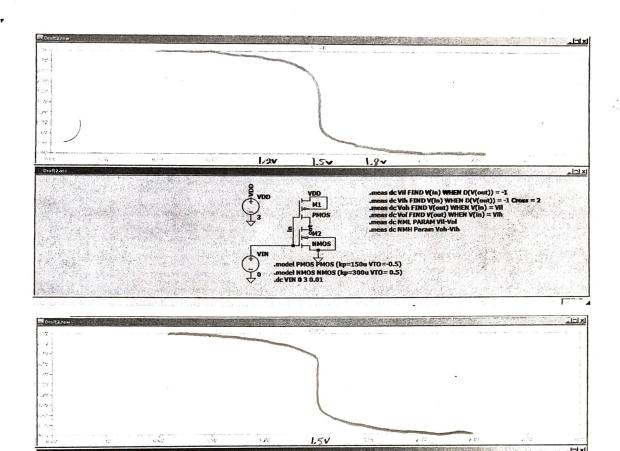
Gabriel Emerson gte0002 CMOS HWI Due 3/10
1.) NMO: PMGS 0.25 - CMGS KP= 150 MA K
KP= 300 WAT KP= 150 Va
Vto= 0.54 Vto=-0.54
$\frac{V_{PP}=3v}{V_{PP}=\frac{300}{150}\cdot 2=\frac{4}{1}}$
NMOS PMOS W= 0.5mm W= 1mm
L= 0.25 m L= 0.25 m
2) For CMOS:
a.) VL = OV VH = 3V
b.) Standby power consumption = OV
C.) Ve and VH will be the same.
d.) VDD->4V: Standby power consumption = OV
e) VIL = 1.25V VIH= 1.75V
VOH = 2.75V VOL = 0.25V
f.) Noice Margin Low->1 Noice Margin High->1
9.) Symmetry remains but it is shifted to 2v due to Upo being 4v. The circuit does
still work like an inverter. However the NML
and NMH will increase which is something
we do not want.

3a) Vin= Iv, Vin= 2V (300)(2)(1-0.5)=75mA ->IDS, NMOS ISD===(150)(4)(-2-(-0.5))=675mA, PMOS IDS sat = = = (150)(2)(2-0.5)=675 mA, NMOS IDS sat = = = (150)(4)(-1-(-0.5))=75 mA, PMOS (14,75mA) (2.54, 75mA) (84. USmV. 75mA) hand calculations are close to simulations.



M1 PMOS Vout

model PMOS PMOS (kp=150u VTO=-0.5) model NMOS NMOS (kp=300u VTO= 0.5) dc VIN 0 3 0.01

- wanter and the second

```
Instance "m2": Length shorter than recommended for a level 1 MOSTRI.
Instance "m2": Width narrower than recommended for a level 1 MOSTRI.
Instance "m1": Length shorter than recommended for a level 1 MOSTRI.
Instance "m1": Width marrower than recommended for a level 1 MOSTRI.
Instance "m1": Width marrower than recommended for a level 1 MOSTRI.

vil: v(in)=1.75002 at 1.24998
vih: v(in)=1.75002 at 1.24998
vol: v(out)=0.24998 at 1.75002
nm1: vil-vol=0.24998 at 1.75002
nm1: vil-vol=0.24998 at 1.75002
nm1: vil-vol=0.2999999
nmh: voh-vih=1

Date: Thu Peb 28 11:38:56 2019
Total elapsed time: 0.102 seconds.

thom = 27
temp = 27
method = trap
totiter = 637
traniter = 0
tranpoints = 0
accept = 0
rejected = 0
matrix size = 5
fillins = 0
solver = Hormal
Matrix Compiler1: 132 bytes object code size 0.1/0.1/[0.1]
```

